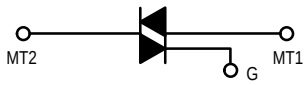
MAC229FP Series MAC229AFP Series

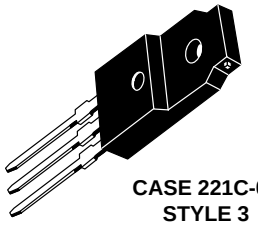
Triacs
Silicon Bidirectional Triode Thyristors

. . . designed primarily for industrial and consumer applications for full wave control of ac loads such as appliance controls, heater controls, motor controls, and other power switching applications.

- All Diffused and Glass-Passivated Junctions for Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal resistance and High Heat Dissipation
- Center Gate Geometry for Uniform Current Spreading
- Gate Triggering Guaranteed in Three Modes (MAC229FP Series) or Four Modes (MAC229AFP Series)

TRIACs
8 AMPERES RMS
200 thru 800 VOLTS





CASE 221C-02
STYLE 3

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted.)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage(1) (T_J = –40 to 110°C, 1/2 Sine Wave 50 to 60 Hz, Gate Open) MAC229-4FP, MAC229A4FP MAC229-6FP, MAC229A6FP MAC229-8FP, MAC229A8FP MAC229-10FP, MAC229A10FP	V_{DRM}	 200 400 600 800	Volts
On-State RMS Current (T_C = 80°C) Full Cycle Sine Wave 50 to 60 Hz	$I_{T(RMS)}$	8	Amps
Peak Non-repetitive Surge Current (One Full Cycle 60 Hz, T_J = 110°C)	I_{TSM}	80	Amps
Circuit Fusing (t = 8.3 ms)	I^2t	26	A^2s
Peak Gate Current (t ≤ 2 µs)	I_{GM}	±2	Amps
Peak Gate Voltage (t ≤ 2 µs)	V_{GM}	±10	Volts
Peak Gate Power (t ≤ 2 µs)	P_{GM}	20	Watts
Average Gate Power (T_C = 80°C, t ≤ 8.3 ms)	$P_{G(AV)}$	0.5	Watts
Operating Junction Temperature Range	T_J	–40 to 110	°C
Storage Temperature Range	T_{stg}	–40 to 150	°C
Mounting Torque		8	in. lb.

1. V_{DRM} for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.
2. The case temperature reference point for all TC measurements is a point on the center lead of the package as close as possible to the plastic body.

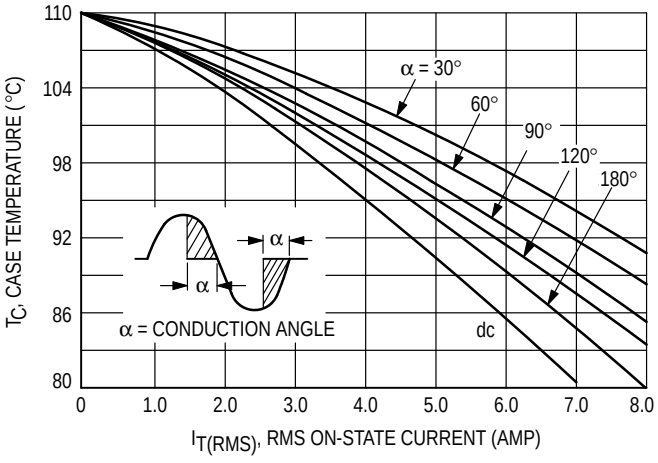
THERMAL CHARACTERISTICS

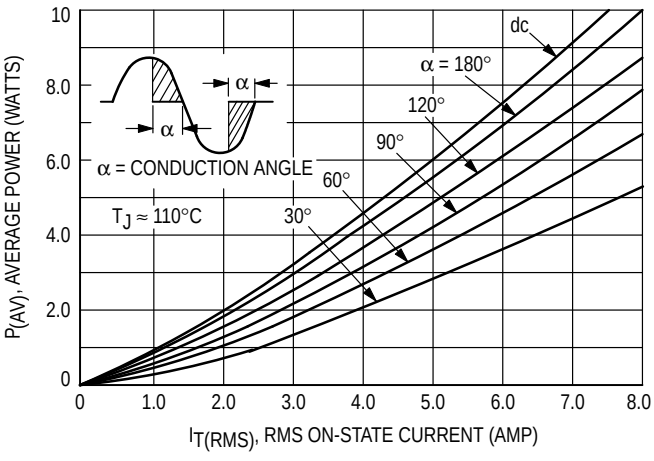
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.2	°C/W
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2 (typ)	°C/W
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C and either polarity of MT2 to MT1 voltage unless otherwise noted.)

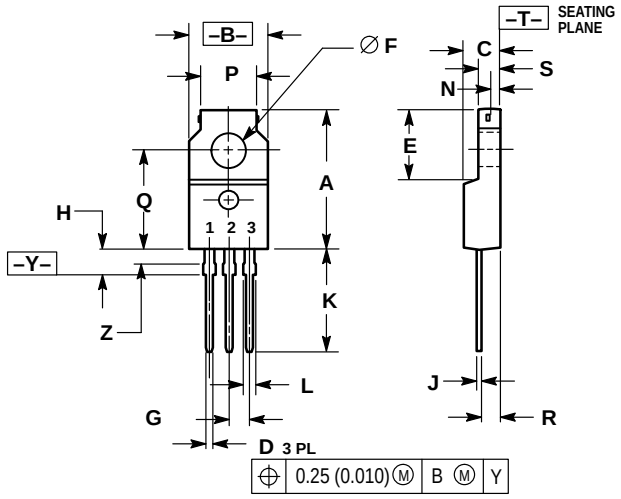
Characteristic	Symbol	Min	Typ	Max	Unit
Peak Blocking Current(1)	I_{DRM}				
(V_D = Rated V_{DRM}, Open Gate) T_J = 25°C		—	—	10	μA
T_J = 110°C		—	—	2	mA
Peak On-State Voltage	V_{TM}	—	—	1.8	Volts
(I_{TM} = 11 A Peak, Pulse Width ≤ 2 ms, Duty Cycle ≤ 2%)					
Gate Trigger Current (Continuous dc)	I_{GT}				mA
(V_D = 12 V, R_L = 100 Ω)					
MT2(+), G(+); MT2(+), G(–); MT2(–), G(–)		—	—	5	
MT2(–), G(+) "A" Suffix Only		—	—	10	
Gate Trigger Voltage (Continuous dc)	V_{GT}				Volts
(V_D = 12 V, R_L = 100 Ω)					
MT2(+), G(+); MT2(+), G(–); MT2(–), G(–)		—	—	2	
MT2(–), G(+) "A" Suffix Only		—	—	2.5	
(V_D = Rated V_{DRM}, T_C = 110°C, R_L = 10 k)					
MT2(+), G(+); MT2(+), G(–); MT2(–), G(–)		0.2	—	—	
MT2(–), G(+) "A" Suffix Only		0.2	—	—	
Holding Current	I_H	—	—	15	mA
(V_D = 12 Vdc, I_{TM} = 200 mA, Gate Open)					
Gate-Controlled Turn-On Time	t_{gt}	—	1.5	—	μs
(V_D = Rated V_{DRM}, I_{TM} = 16 A Peak, I_G = 30 mA)					
Critical Rate of Rise of Off-State Voltage	dv/dt	—	25	—	V/μs
(V_D = Rated V_{DRM}, Exponential Waveform, T_C = 110°C)					
Critical Rate of Rise of Commutation Voltage	dv/dt(c)	—	5	—	V/μs
(V_D = Rated V_{DRM}, I_{TM} = 11.3 A, Commutating di/dt = 4.1 A/ms, Gate Unenergized, T_C = 80°C)					

1. Ratings apply for open gate conditions. Devices shall not be tested with a constant current source for blocking voltage such that the voltage applied exceeds the rated blocking voltage.





PACKAGE DIMENSIONS



STYLE 3:
PIN 1. MT 1
2. MT 2
3. GATE

NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.680	0.700	17.28	17.78
B	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
H	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049	—	1.25	—
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

CASE 221C–02

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